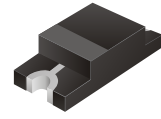


# SMD Schottky Barrier Diode

## CDBS0130

$I_o = 100\text{mA}$   
 $V_R = 30\text{ Volts}$

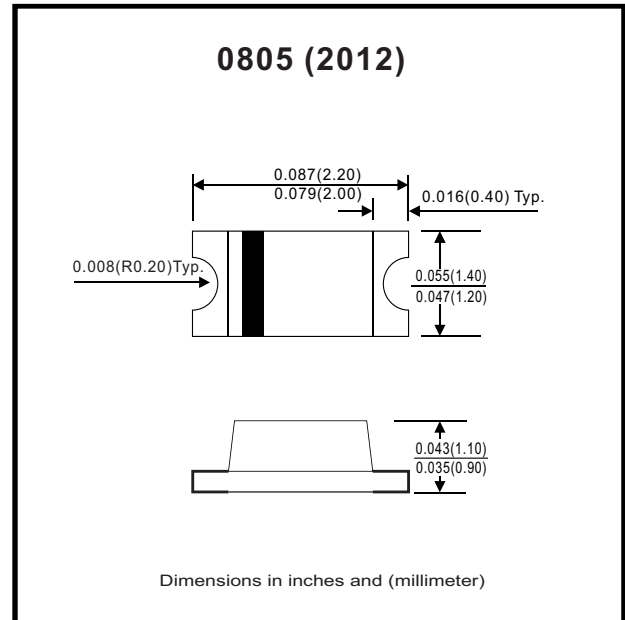


### Features

- Designed for mounting on small surface
- Extremely thin package
- Low stored charge
- Majority carrier conduction

### Mechanical data

- Case: 0805(2012) Standard package, molded plastic
- Terminals: Solder plated, solderable per MIL-STD-750, method 2026
- Polarity: Indicated by cathode band
- Mounting position: Any
- Weight: 0.0048 gram (approximately)



### Maximum Rating ( at $T_A = 25^\circ\text{C}$ unless otherwise noted )

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive peak reverse voltage		$V_{RRM}$			35	V
Reverse voltage		$V_R$			30	V
Average forward current		$I_o$			100	mA
Forward current , surge peak	8.3 ms single half sine-wave superimposed on rate load( JEDEC method )	$I_{FSM}$		1000		mA
Power Dissipation		$P_d$			250	mW
Storage temperature		$T_{STG}$	-40		+125	$^\circ\text{C}$
Junction temperature		$T_j$	-40		+125	$^\circ\text{C}$

### Electrical Characteristics ( at $T_A = 25^\circ\text{C}$ unless otherwise noted )

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 100\text{ mADC}$	$V_F$			0.44	V
Reverse current	$V_R = 30\text{ V}$	$I_R$			30	$\mu\text{A}$
Capacitance between terminals	$f = 1\text{MHz}$ , and 10 VDC reverse voltage	$C_T$		10		pF

## RATING AND CHARACTERISTIC CURVES (CDBS0130)

Fig. 1 - Forward characteristics

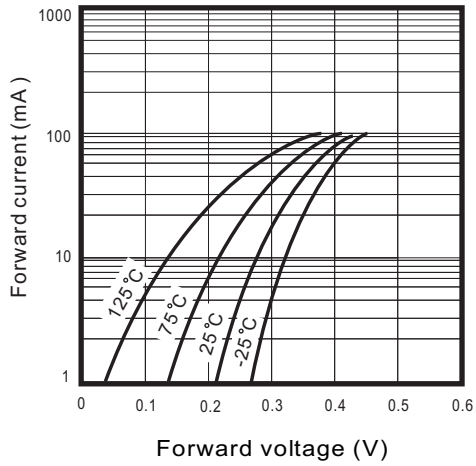


Fig. 2 - Reverse characteristics

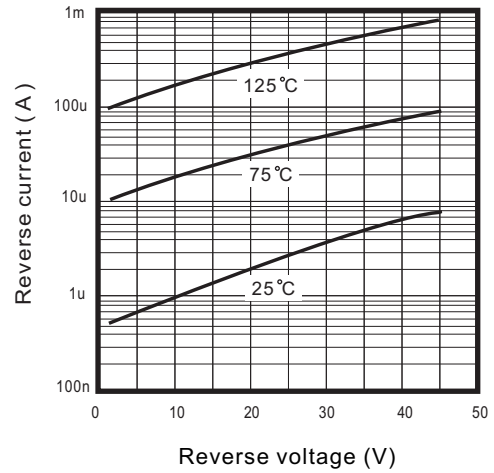


Fig. 3 - Capacitance between terminals characteristics

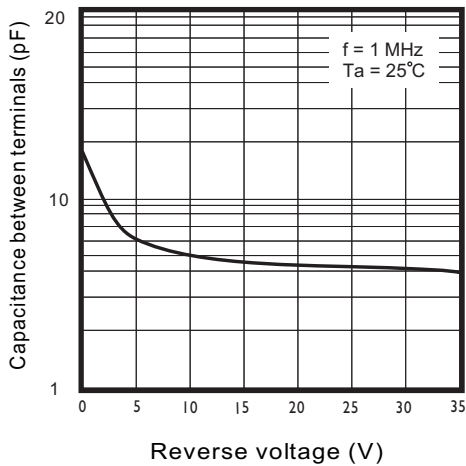


Fig. 4 - Current derating curve

